

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## General Purpose Transistors

### NPN and PNP Silicon

These transistors are designed for general purpose amplifier applications. They are housed in the SOT-323/SC-70 package which is designed for low power surface mount applications.

#### Features

- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage MMBT3904WT1 MMBT3906WT1	$V_{CEO}$	40 -40	Vdc
Collector - Base Voltage MMBT3904WT1 MMBT3906WT1	$V_{CBO}$	60 -40	Vdc
Emitter - Base Voltage MMBT3904WT1 MMBT3906WT1	$V_{EBO}$	6.0 -5.0	Vdc
Collector Current - Continuous MMBT3904WT1 MMBT3906WT1	$I_C$	200 -200	mAdc

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation (Note 1) @ $T_A = 25^\circ\text{C}$	$P_D$	150	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	$T_J, T_{stg}$	-55 to +150	$^\circ\text{C}$

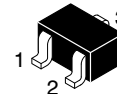
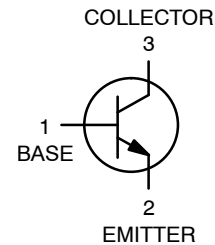
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Device mounted on FR4 glass epoxy printed circuit board using the minimum recommended footprint.



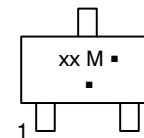
ON Semiconductor®

<http://onsemi.com>



SC-70 (SOT-323)  
CASE 419  
STYLE 3

#### MARKING DIAGRAM



xx = AM for MMBT3904WT1  
= 2A for MMBT3906WT1  
M = Date Code\*  
▪ = Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### ORDERING INFORMATION

Device	Package	Shipping†
MMBT3904WT1G	SC-70/ SOT-323 (Pb-Free)	3000/Tape & Reel
MMBT3906WT1G	SC-70/ SOT-323 (Pb-Free)	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Collector – Emitter Breakdown Voltage (Note 2) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0) (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , I <sub>B</sub> = 0)	MMBT3904WT1 MMBT3906WT1	V <sub>(BR)CEO</sub>	40 -40	- -	V <sub>dc</sub>
Collector – Base Breakdown Voltage (I <sub>C</sub> = 10 μA <sub>dc</sub> , I <sub>E</sub> = 0) (I <sub>C</sub> = -10 μA <sub>dc</sub> , I <sub>E</sub> = 0)	MMBT3904WT1 MMBT3906WT1	V <sub>(BR)CBO</sub>	60 -40	- -	V <sub>dc</sub>
Emitter – Base Breakdown Voltage (I <sub>E</sub> = 10 μA <sub>dc</sub> , I <sub>C</sub> = 0) (I <sub>E</sub> = -10 μA <sub>dc</sub> , I <sub>C</sub> = 0)	MMBT3904WT1 MMBT3906WT1	V <sub>(BR)EBO</sub>	6.0 -5.0	- -	V <sub>dc</sub>
Base Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> ) (V <sub>CE</sub> = -30 V <sub>dc</sub> , V <sub>EB</sub> = -3.0 V <sub>dc</sub> )	MMBT3904WT1 MMBT3906WT1	I <sub>BL</sub>	- -	50 -50	nA <sub>dc</sub>
Collector Cutoff Current (V <sub>CE</sub> = 30 V <sub>dc</sub> , V <sub>EB</sub> = 3.0 V <sub>dc</sub> ) (V <sub>CE</sub> = -30 V <sub>dc</sub> , V <sub>EB</sub> = -3.0 V <sub>dc</sub> )	MMBT3904WT1 MMBT3906WT1	I <sub>CEx</sub>	- -	50 -50	nA <sub>dc</sub>
<b>ON CHARACTERISTICS (Note 2)</b>					
DC Current Gain (I <sub>C</sub> = 0.1 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 1.0 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = 100 mA <sub>dc</sub> , V <sub>CE</sub> = 1.0 V <sub>dc</sub> ) (I <sub>C</sub> = -0.1 mA <sub>dc</sub> , V <sub>CE</sub> = -1.0 V <sub>dc</sub> ) (I <sub>C</sub> = -1.0 mA <sub>dc</sub> , V <sub>CE</sub> = -1.0 V <sub>dc</sub> ) (I <sub>C</sub> = -10 mA <sub>dc</sub> , V <sub>CE</sub> = -1.0 V <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , V <sub>CE</sub> = -1.0 V <sub>dc</sub> ) (I <sub>C</sub> = -100 mA <sub>dc</sub> , V <sub>CE</sub> = -1.0 V <sub>dc</sub> )	MMBT3904WT1     MMBT3906WT1	h <sub>FE</sub>	40 70 100 60 30 60 80 100 60 30	- - 300 - - - - 300 - -	-
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -10 mA <sub>dc</sub> , I <sub>B</sub> = -1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , I <sub>B</sub> = -5.0 mA <sub>dc</sub> )	MMBT3904WT1  MMBT3906WT1	V <sub>CE(sat)</sub>	- - - -	0.2 0.3 -0.25 -0.4	V <sub>dc</sub>
Base – Emitter Saturation Voltage (I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = 50 mA <sub>dc</sub> , I <sub>B</sub> = 5.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -10 mA <sub>dc</sub> , I <sub>B</sub> = -1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -50 mA <sub>dc</sub> , I <sub>B</sub> = -5.0 mA <sub>dc</sub> )	MMBT3904WT1  MMBT3906WT1	V <sub>BE(sat)</sub>	0.65 - -0.65 -	0.85 0.95 -0.85 -0.95	V <sub>dc</sub>

2. Pulse Test: Pulse Width ≤ 300 μs; Duty Cycle ≤ 2.0%.

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
<b>SMALL-SIGNAL CHARACTERISTICS</b>				
Current-Gain – Bandwidth Product (I <sub>C</sub> = 10 mA <sub>dc</sub> , V <sub>CE</sub> = 20 V <sub>dc</sub> , f = 100 MHz) (I <sub>C</sub> = -10 mA <sub>dc</sub> , V <sub>CE</sub> = -20 V <sub>dc</sub> , f = 100 MHz)	f <sub>T</sub>	300 250	– –	MHz
Output Capacitance (V <sub>CB</sub> = 5.0 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz) (V <sub>CB</sub> = -5.0 V <sub>dc</sub> , I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>obo</sub>	– –	4.0 4.5	pF
Input Capacitance (V <sub>EB</sub> = 0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz) (V <sub>EB</sub> = -0.5 V <sub>dc</sub> , I <sub>C</sub> = 0, f = 1.0 MHz)	C <sub>ibo</sub>	– –	8.0 10.0	pF
Input Impedance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz) (V <sub>CE</sub> = -10 V <sub>dc</sub> , I <sub>C</sub> = -1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>ie</sub>	1.0 2.0	10 12	k Ω
Voltage Feedback Ratio (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz) (V <sub>CE</sub> = -10 V <sub>dc</sub> , I <sub>C</sub> = -1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>re</sub>	0.5 0.1	8.0 10	X 10 <sup>-4</sup>
Small-Signal Current Gain (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz) (V <sub>CE</sub> = -10 V <sub>dc</sub> , I <sub>C</sub> = -1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>fe</sub>	100 100	400 400	–
Output Admittance (V <sub>CE</sub> = 10 V <sub>dc</sub> , I <sub>C</sub> = 1.0 mA <sub>dc</sub> , f = 1.0 kHz) (V <sub>CE</sub> = -10 V <sub>dc</sub> , I <sub>C</sub> = -1.0 mA <sub>dc</sub> , f = 1.0 kHz)	h <sub>oe</sub>	1.0 3.0	40 60	μmhos
Noise Figure (V <sub>CE</sub> = 5.0 V <sub>dc</sub> , I <sub>C</sub> = 100 μA <sub>dc</sub> , R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz) (V <sub>CE</sub> = -5.0 V <sub>dc</sub> , I <sub>C</sub> = -100 μA <sub>dc</sub> , R <sub>S</sub> = 1.0 k Ω, f = 1.0 kHz)	NF	– –	5.0 4.0	dB

## SWITCHING CHARACTERISTICS

Characteristic	Condition	Symbol	Min	Max	Unit
Delay Time	(V <sub>CC</sub> = 3.0 V <sub>dc</sub> , V <sub>BE</sub> = -0.5 V <sub>dc</sub> ) (V <sub>CC</sub> = -3.0 V <sub>dc</sub> , V <sub>BE</sub> = 0.5 V <sub>dc</sub> )	t <sub>d</sub>	– –	35 35	ns
Rise Time	(I <sub>C</sub> = 10 mA <sub>dc</sub> , I <sub>B1</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>C</sub> = -10 mA <sub>dc</sub> , I <sub>B1</sub> = -1.0 mA <sub>dc</sub> )	t <sub>r</sub>	– –	35 35	ns
Storage Time	(V <sub>CC</sub> = 3.0 V <sub>dc</sub> , I <sub>C</sub> = 10 mA <sub>dc</sub> ) (V <sub>CC</sub> = -3.0 V <sub>dc</sub> , I <sub>C</sub> = -10 mA <sub>dc</sub> )	t <sub>s</sub>	– –	200 225	ns
Fall Time	(I <sub>B1</sub> = I <sub>B2</sub> = 1.0 mA <sub>dc</sub> ) (I <sub>B1</sub> = I <sub>B2</sub> = -1.0 mA <sub>dc</sub> )	t <sub>f</sub>	– –	50 75	ns

### MMBT3904WT1

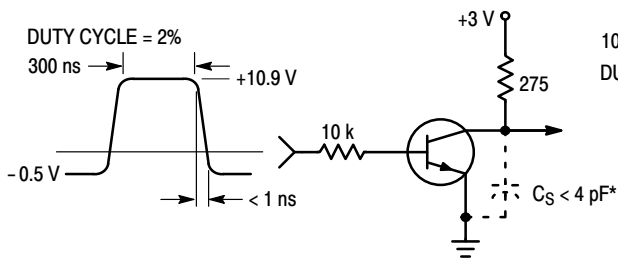


Figure 1. Delay and Rise Time Equivalent Test Circuit

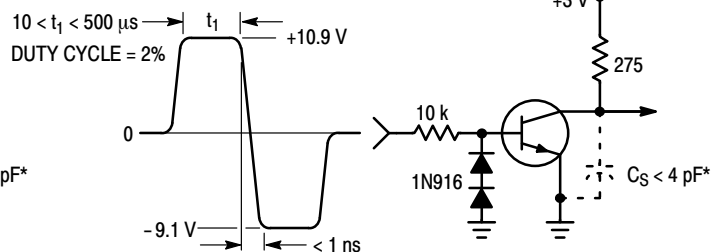


Figure 2. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3904WT1

### TYPICAL TRANSIENT CHARACTERISTICS

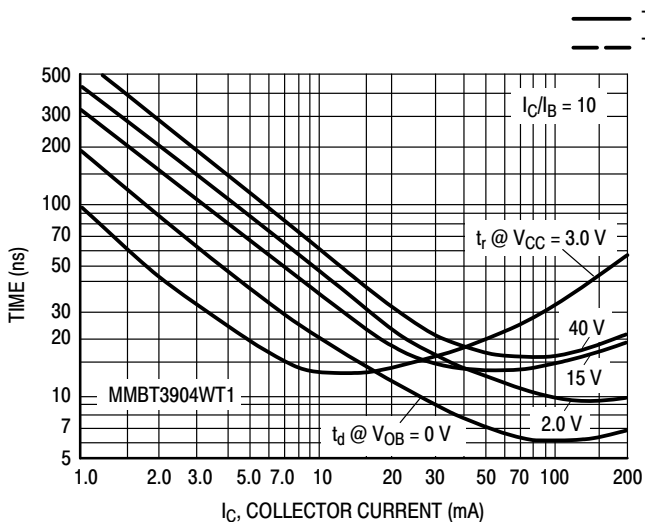


Figure 3. Turn-On Time

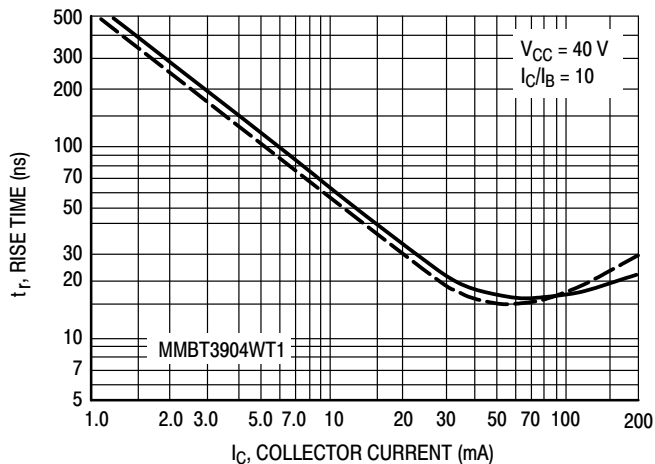


Figure 4. Rise Time

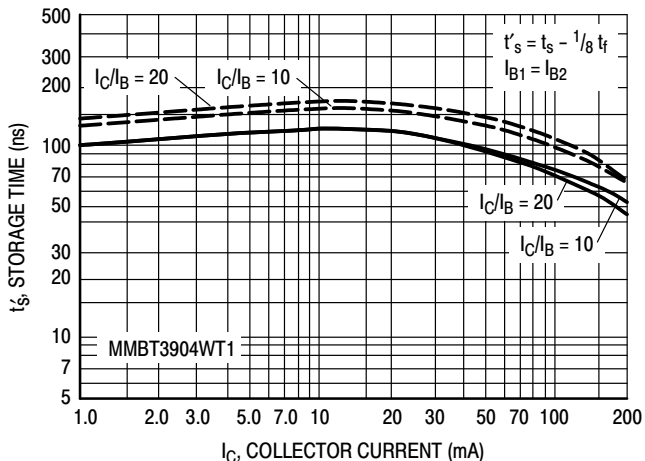


Figure 5. Storage Time

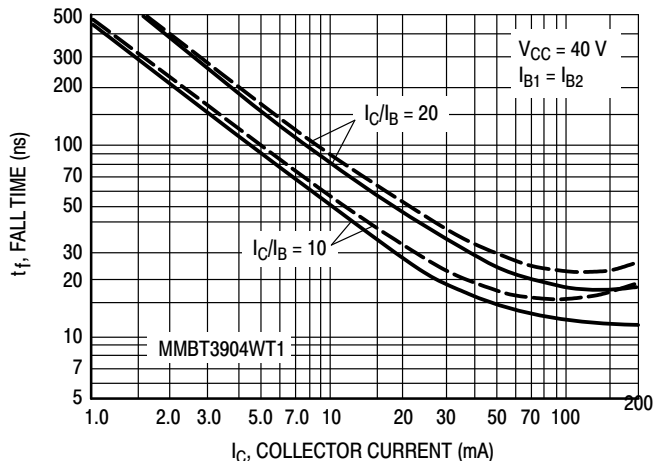


Figure 6. Fall Time

### TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = 5.0$  Vdc,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

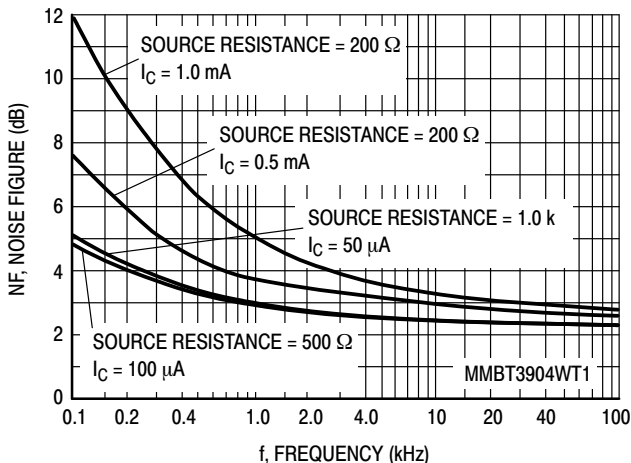


Figure 7. Noise Figure

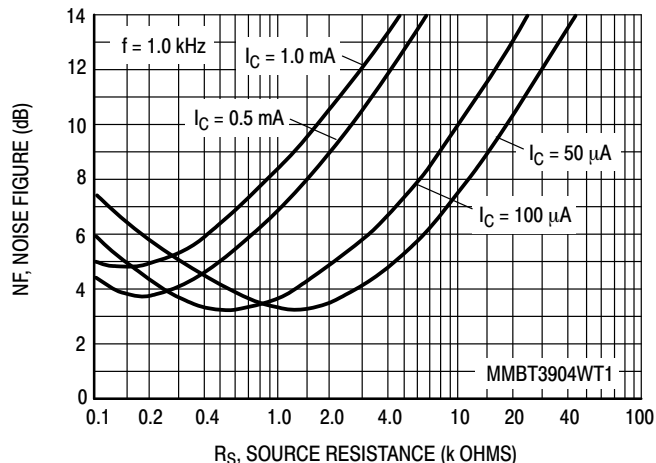


Figure 8. Noise Figure

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3904WT1

### h PARAMETERS

( $V_{CE} = 10 \text{ Vdc}$ ,  $f = 1.0 \text{ kHz}$ ,  $T_A = 25^\circ\text{C}$ )

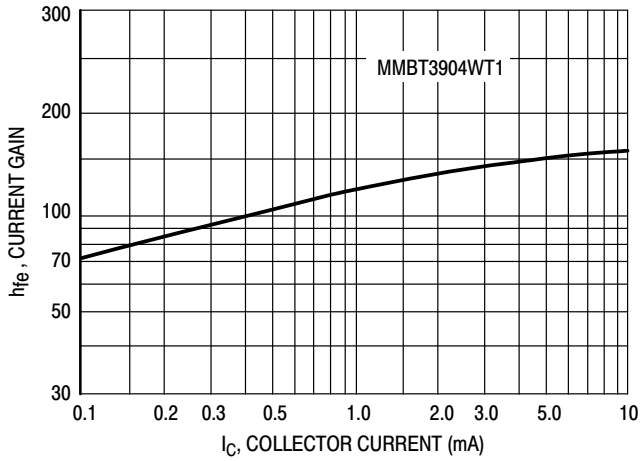


Figure 9. Current Gain

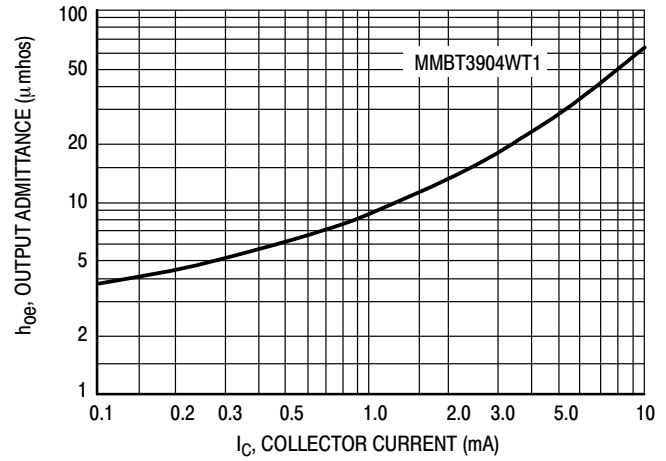


Figure 10. Output Admittance

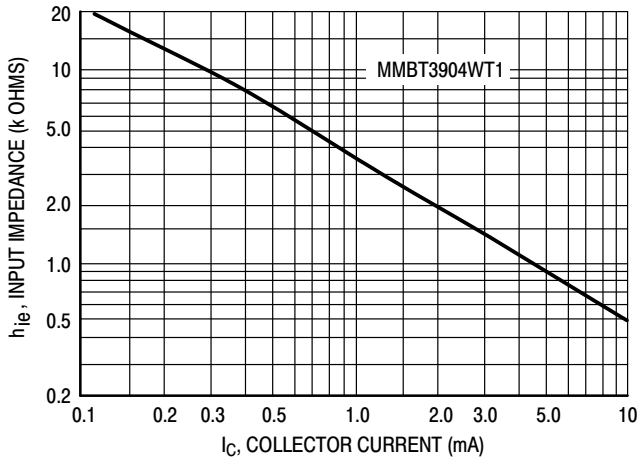


Figure 11. Input Impedance

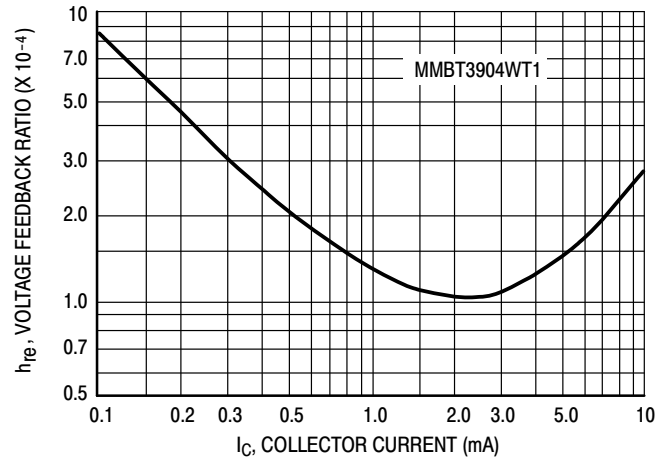


Figure 12. Voltage Feedback Ratio

### TYPICAL STATIC CHARACTERISTICS

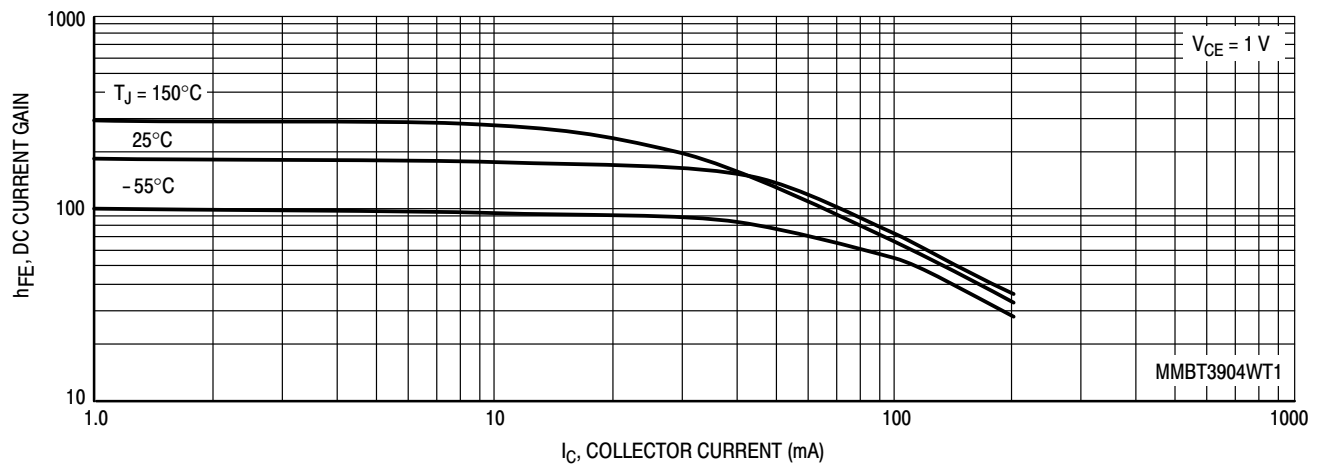


Figure 13. DC Current Gain

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3904WT1

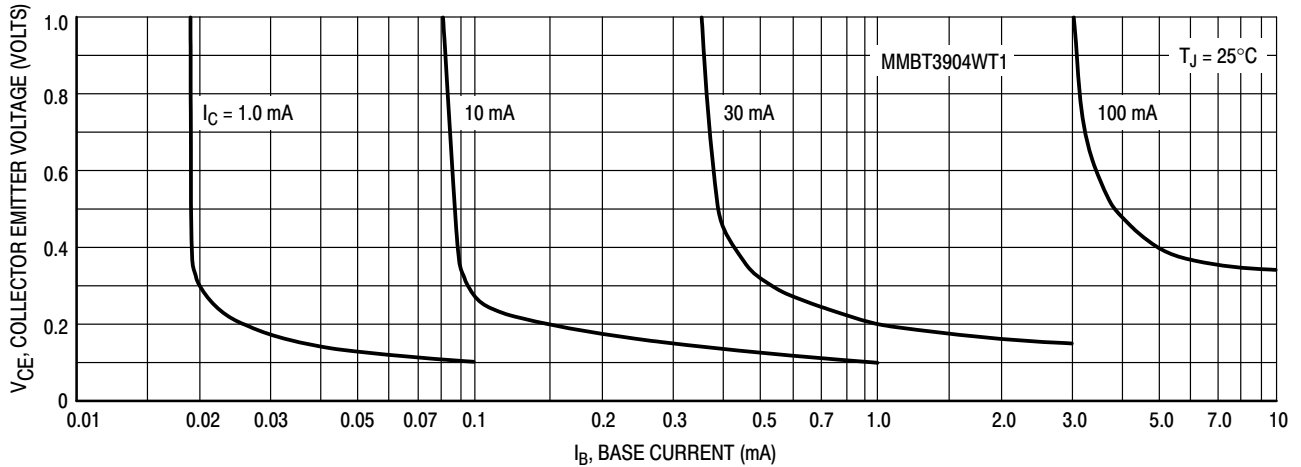


Figure 14. Collector Saturation Region

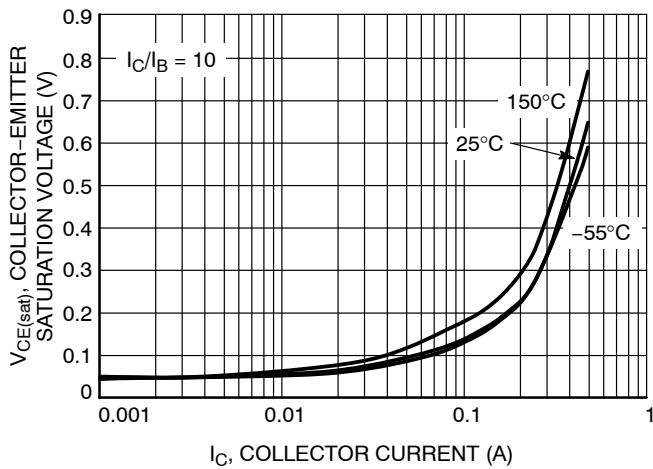


Figure 15. Collector Emitter Saturation Voltage vs. Collector Current

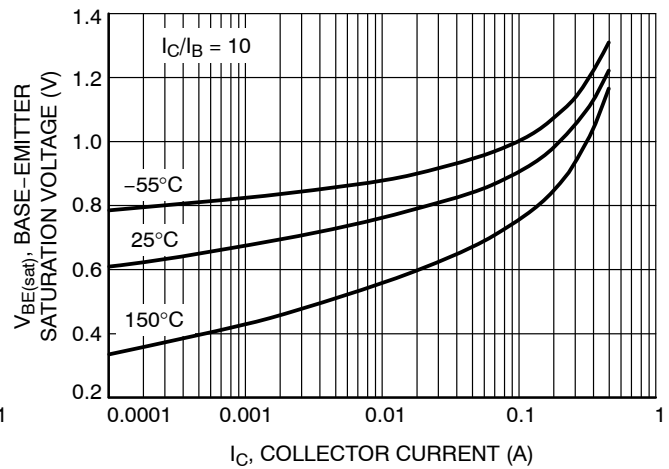


Figure 16. Base Emitter Saturation Voltage vs. Collector Current

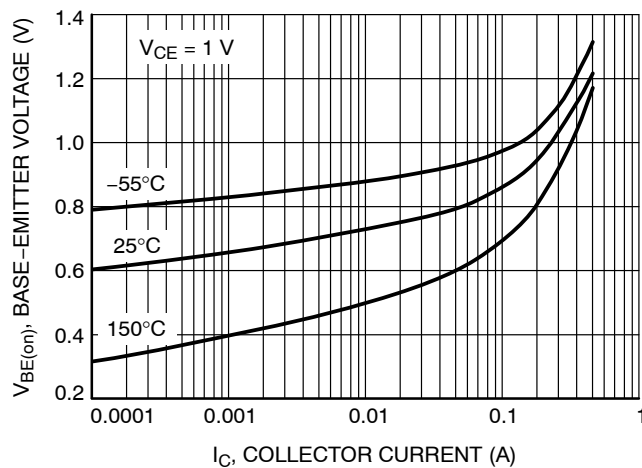


Figure 17. Base Emitter Voltage vs. Collector Current

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3904WT1

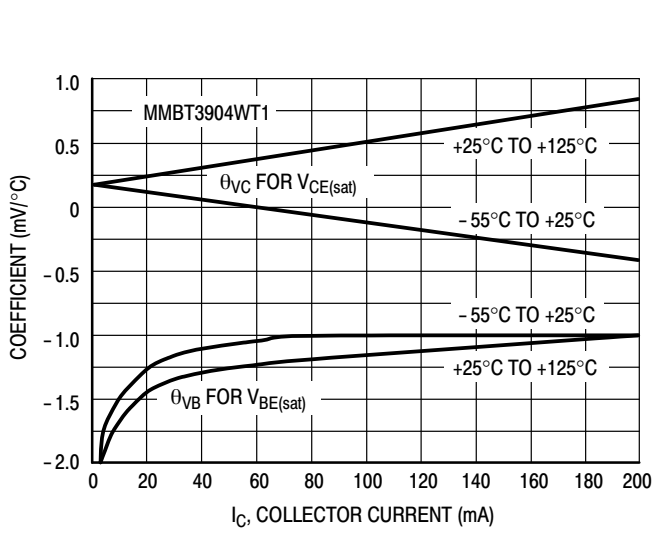


Figure 18. Temperature Coefficients

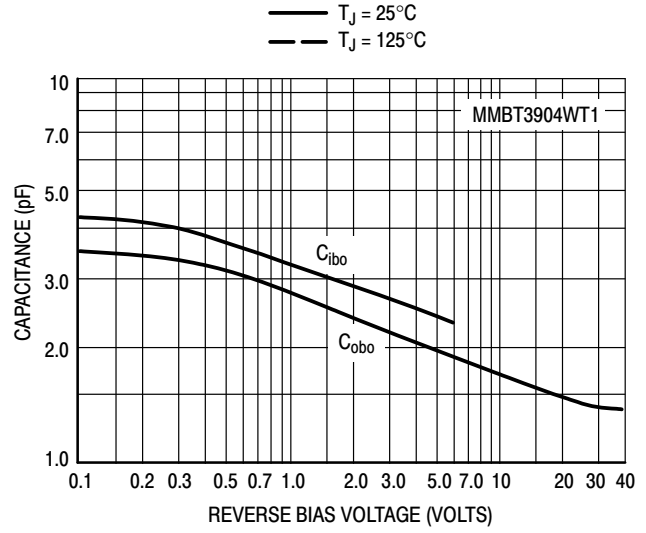


Figure 19. Capacitance

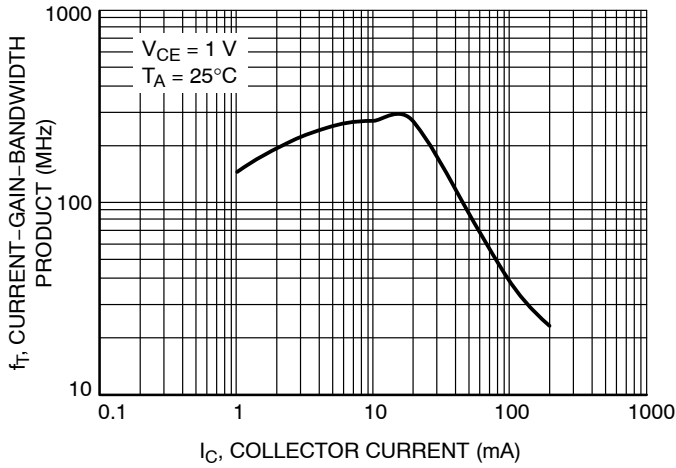


Figure 20. Current Gain Bandwidth Product vs. Collector Current

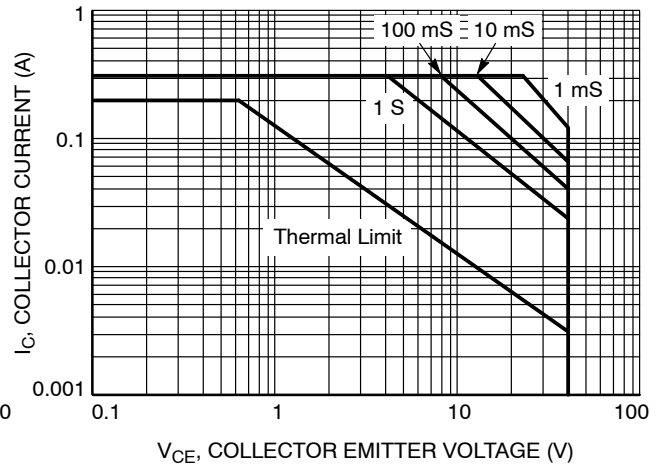


Figure 21. Safe Operating Area

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3906WT1

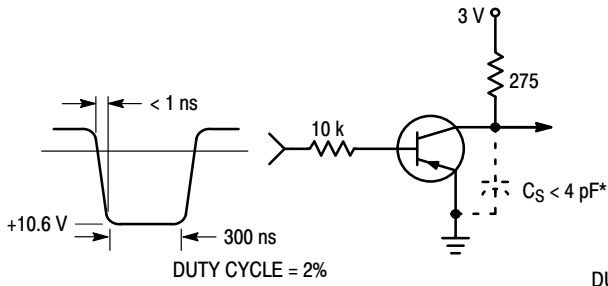


Figure 22. Delay and Rise Time Equivalent Test Circuit

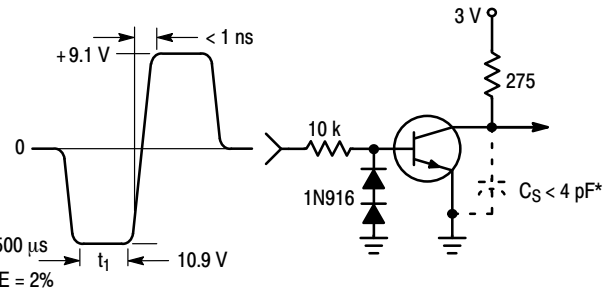


Figure 23. Storage and Fall Time Equivalent Test Circuit

\* Total shunt capacitance of test jig and connectors

## TYPICAL TRANSIENT CHARACTERISTICS

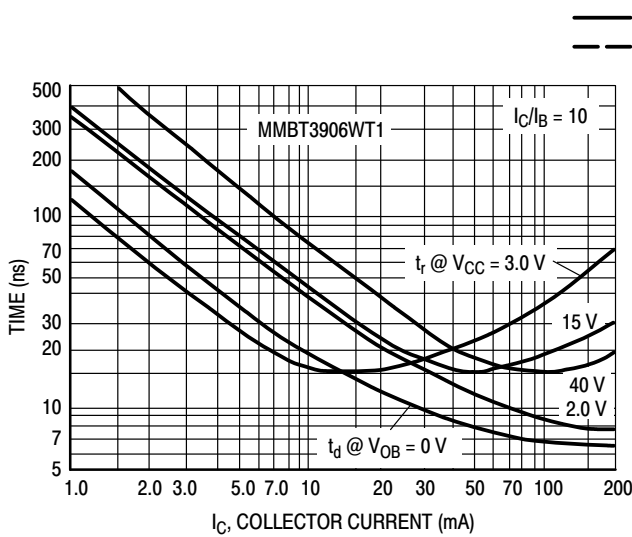


Figure 24. Turn-On Time

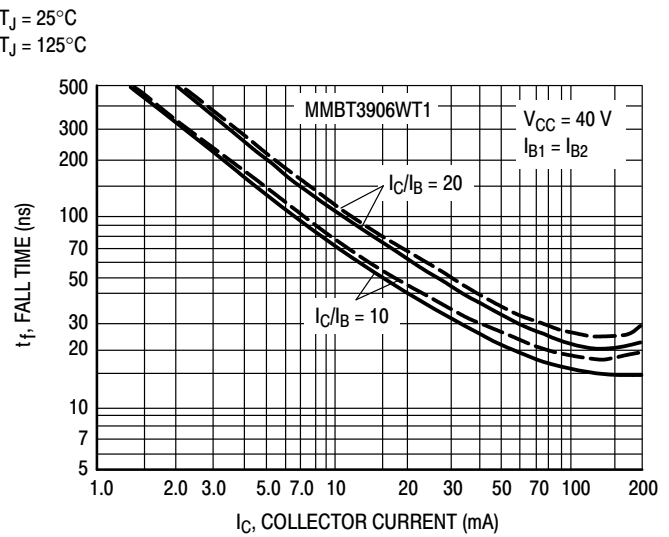


Figure 25. Fall Time

## TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

( $V_{CE} = -5.0\text{ Vdc}$ ,  $T_A = 25^\circ\text{C}$ , Bandwidth = 1.0 Hz)

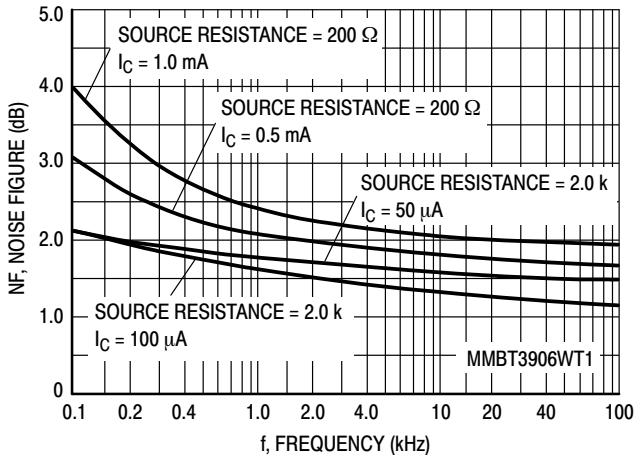


Figure 26.

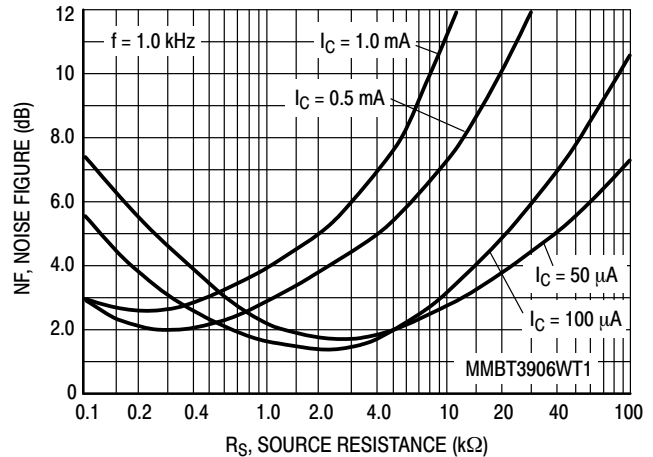


Figure 27.



# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3906WT1

### h PARAMETERS

( $V_{CE} = -10$  Vdc,  $f = 1.0$  kHz,  $T_A = 25^\circ\text{C}$ )

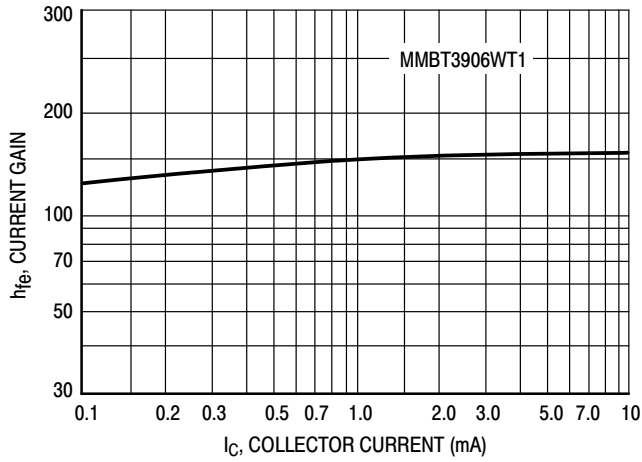


Figure 28. Current Gain

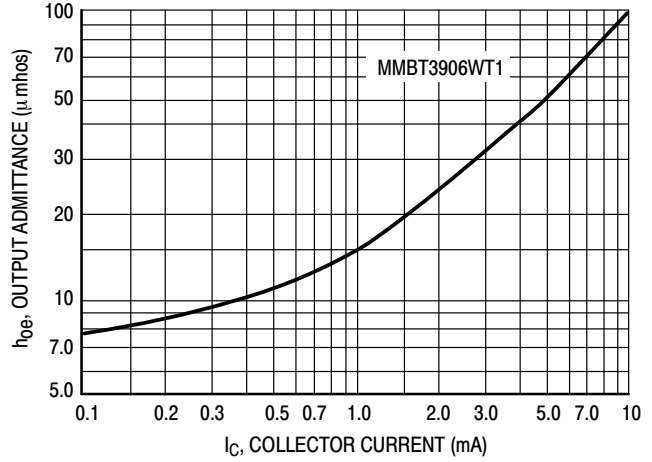


Figure 29. Output Admittance

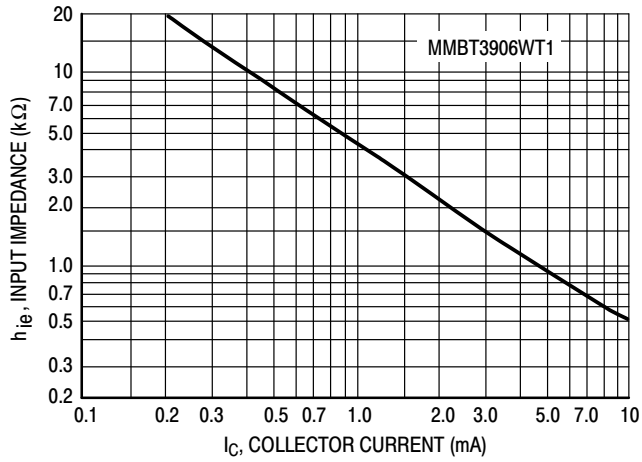


Figure 30. Input Impedance

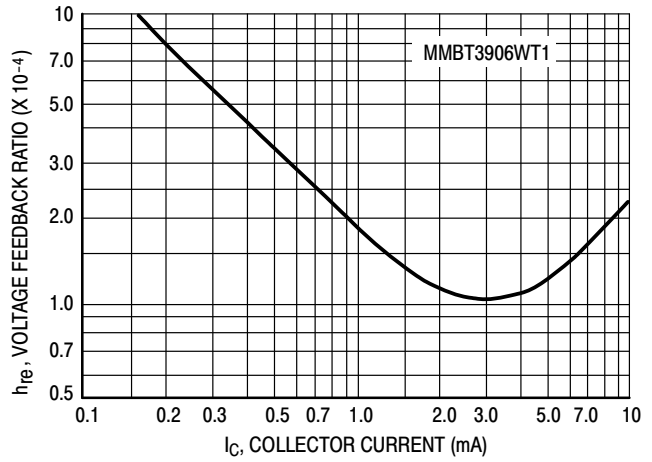


Figure 31. Voltage Feedback Ratio

### STATIC CHARACTERISTICS

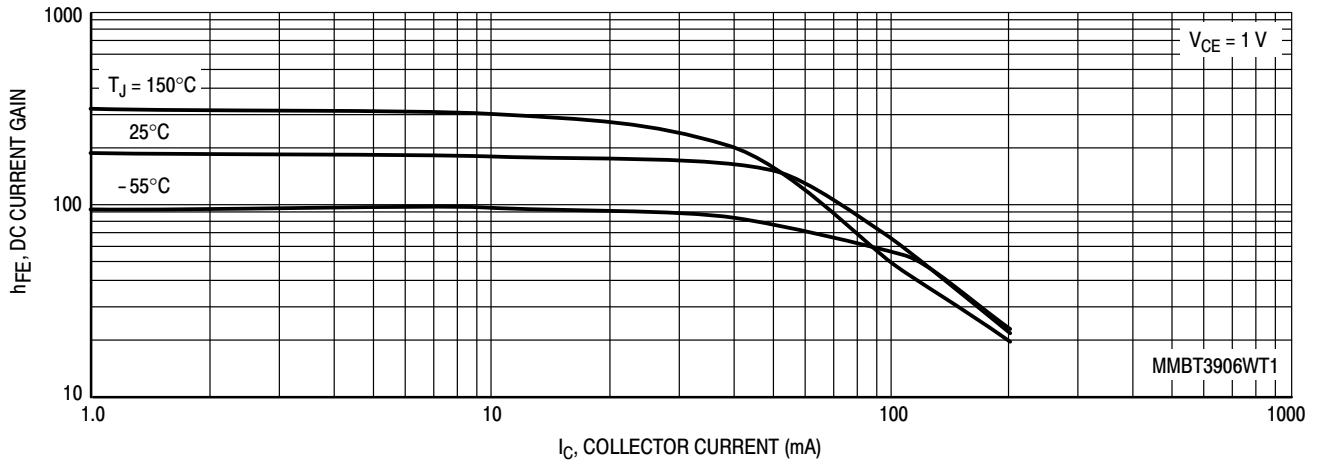


Figure 32. DC Current Gain

MMBT3904WT1, NPN MMBT3906WT1, PNP

MMBT3906WT1

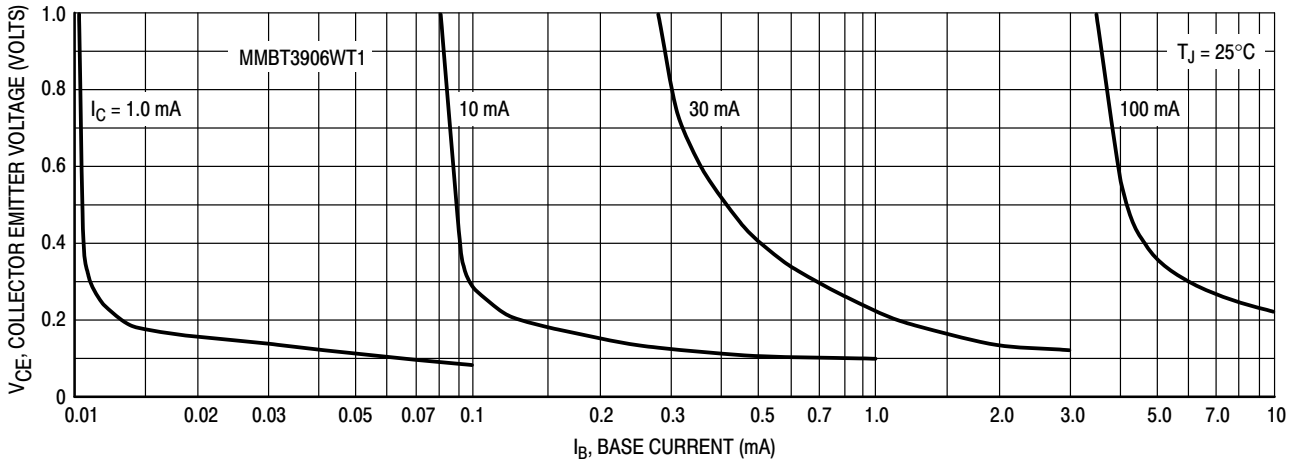


Figure 33. Collector Saturation Region

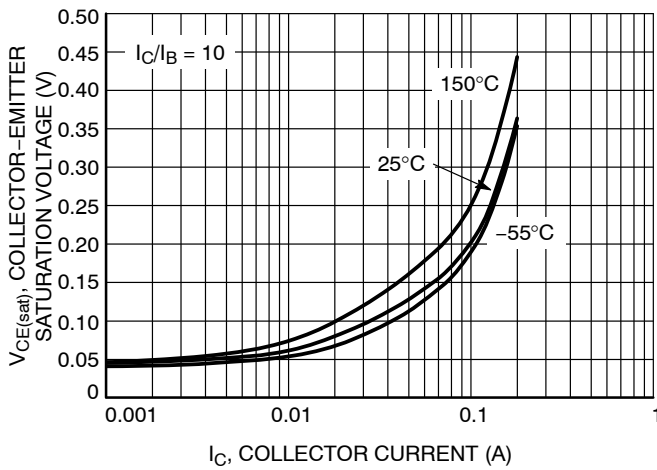


Figure 34. Collector Emitter Saturation Voltage vs. Collector Current

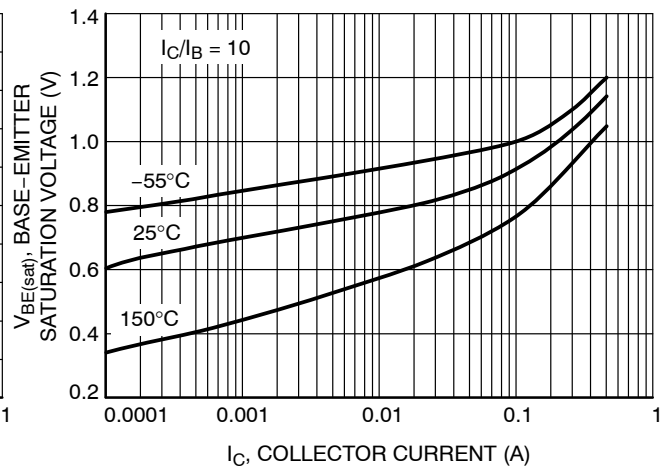


Figure 35. Base Emitter Saturation Voltage vs. Collector Current

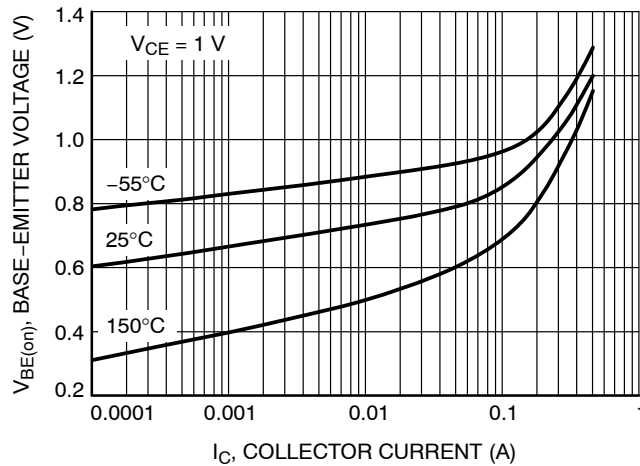


Figure 36. Base Emitter Voltage vs. Collector Current

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## MMBT3906WT1

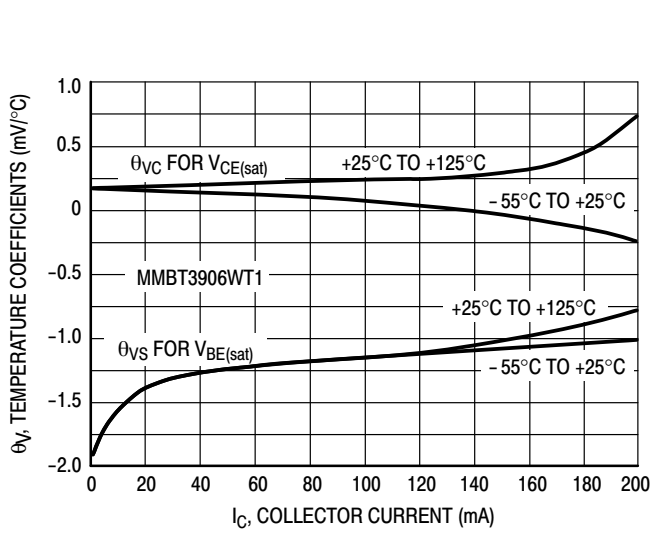


Figure 37. Temperature Coefficients

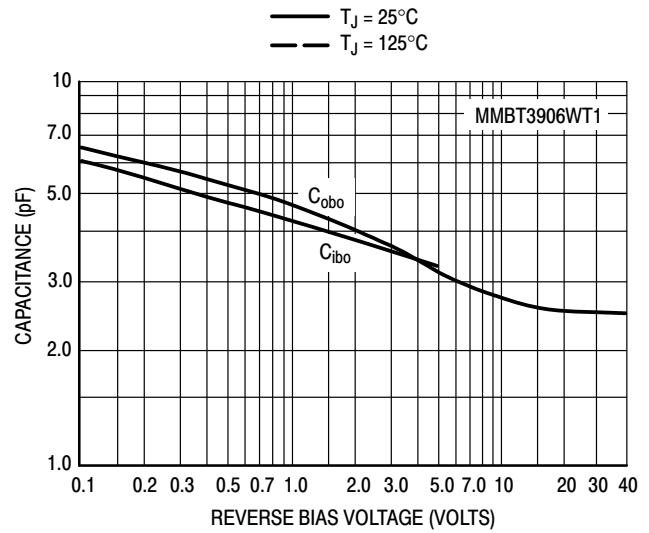


Figure 38. Capacitance

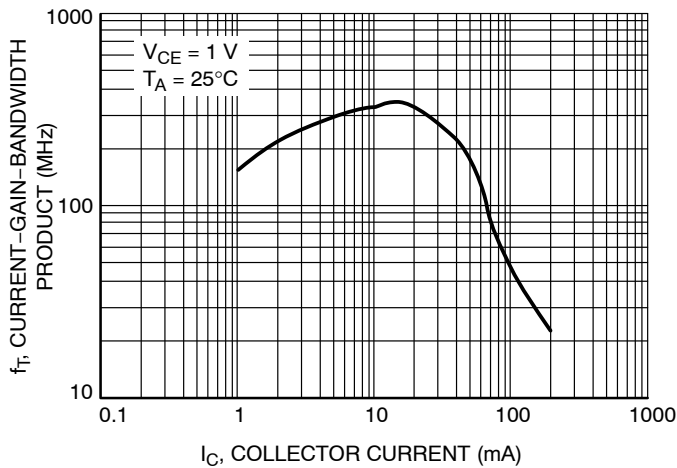


Figure 39. Current Gain Bandwidth Product vs. Collector Current

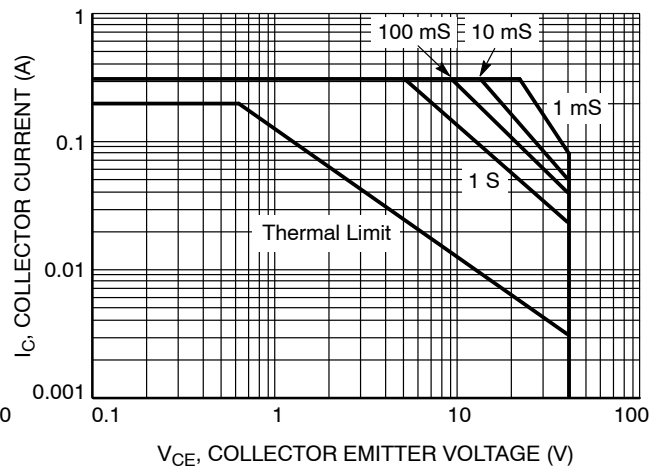
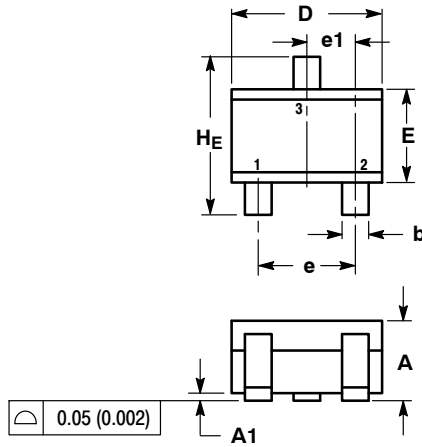


Figure 40. Safe Operating Area

# MMBT3904WT1, NPN MMBT3906WT1, PNP

## PACKAGE DIMENSIONS

SC-70 (SOT-323)  
CASE 419-04  
ISSUE N



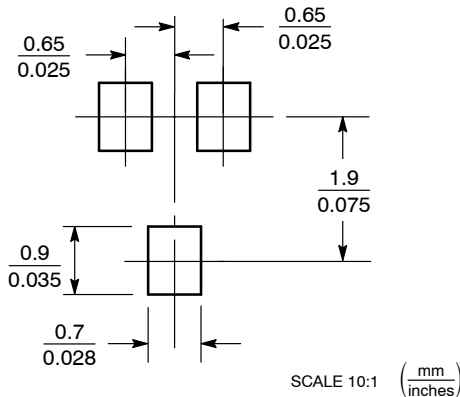
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 REF		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.10	2.20	0.071	0.083	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

STYLE 3:  
PIN 1. BASE  
2. EMITTER  
3. COLLECTOR

### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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